

FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 10873.1333USW1	Application Number: 10/719,412
	Applicant: SUGITA et al.	
	Filing Date: November 21, 2003	Group Art Unit: Unknown


U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Ji Hyung Yu et al. "Magnetic Tunnel Junctions with High Magnetoresistance and Small Bias Voltage Dependence Using Expitaxial NiFe (111) Ferromagnetic Bottom Electrodes", Journal of Applied Physics, Vol. 93, No.10, pp. 8555-8557, May 15, 2003.

23552

PATENT TRADEMARK OFFICE

EXAMINER

DATE CONSIDERED

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EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,312,840	11.2001	Kumagai et al.			
	2001/0053053	12.2001	Saito et al.			
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FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	2000-068569	03.2000	Japan			Abstract	
	2001-236613	08.2001	Japan			Abstract	
	2000-188435	07.2000	Japan			Abstract	
	2002-171012	06.2002	Japan			Abstract	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Koichiro INOMATA, "MRAM Technology Progress and Prospect" Materials Integration Vol. 13, No. 12, P13-18, 2000 (Japanese only)
		T.Miyazaki et al., "Giant Magnetic Tunneling Effect in Fe/Al ₂ O ₃ /Fe Junction", Journal of Magnetism and Magnetic Materials, 139 (1995) L231-L234
		Ping Shang et al., "High-resolution electron microscopy study of tunneling junctions with AlN and Alon barriers", Journal of Applied Physics, Vol. 89, No. 11, pp. 6874-6876, 1 June 2001
		Yasunari SUGITA et al., "Tunneling Magnetoresistance Enhancement for Pt-Added Magnetic Tunnel Junctions", Japanese Journal of Applied Physics, Vol. 41, No. 10A, pp. L1072-1074, October 1, 2002
		Nozomu MATSUKAWA et al., "Thermally stable exchange-biased magnetic tunnel junctions over 400° C" Applied Physics Letter, Vol. 81, No. 25, pp. 4784-4786, December 16, 2002

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6/29/04

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